

MBR20H100CT - MBR20H200CT

20.0 AMPS. Schottky Barrier Rectifiers

TO-220AB



Features

- Plastic material used carries Underwriters Laboratory Classifications 94V-0
- Metal silicon junction, majority carrier conduction
- Low power loss, high efficiency
- High current capability, low forward voltage drop
- High surge capability
- For use in power supply output rectification, power management, instrumentation
- Guardring for overvoltage protection
- High temperature soldering guaranteed: 260°C/10 seconds,0.25"(6.35mm)from case

Mechanical Data

- Cases: JEDEC TO-220AB molded plastic body
- Terminals: Pure tin plated, lead free. solderable per MIL-STD-750, Method 2026
- Polarity: As marked
- Mounting position: Any
- Mounting torque: 5 in. lbs. max Weight: 0.08 ounce, 2.24 grams

.185(4.70) .055(1.40) .16(4.06) .11(2.79) .56(14.22)

Dimensions in inches and (millimeters)

PIN 1

Maximum Ratings and Electrical Characteristics

Rating at 25 °C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load.

For capacitive load, derate current by 20%

Type Number	Symbol	MBR 20H100CT	MBR 20H150CT	MBR 20H200CT	Units
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	100	150	200	V
Maximum RMS Voltage	V_{RMS}	70	105	140	V
Maximum DC Blocking Voltage	V_{DC}	100	150	200	V
Maximum Average Forward Rectified Current at Tc=125°C	I _(AV)	20			Α
Peak Repetitive Forward Current (Rated V _R , Square Wave, 20KHz) at Tc=125°C	I _{FRM}	20			Α
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I _{FSM}	150			Α
Peak Repetitive Reverse Surge Current (Note 1)	I _{RRM}	1.0 0.5		Α	
$\begin{array}{lll} \text{Maximum Instantaneous Forward Voltage at:} \\ \text{(Note 2)} & I_F = 10\text{A, } T_C = 25^{\circ}\text{C} \\ I_F = 10\text{A, } T_C = 125^{\circ}\text{C} \\ I_F = 20\text{A, } T_C = 25^{\circ}\text{C} \\ I_F = 20\text{A, } T_C = 125^{\circ}\text{C} \\ \end{array}$	V _F	0.85 0.75 0.95 0.85	0.88 0.75 0.97 0.85		V
Maximum Instantaneous Reverse Current @ Tc =25 °C at Rated DC Blocking Voltage @ Tc=125 °C (Note 2)	I _R	5 2.0			uA mA
Voltage Rate of Change (Rated V _R)	dV/dt	10,000			V/uS
Maximum Typical Thermal Resistance (Note 3)	R ₀ JC	1.5			°C/W
Operating Junction Temperature Range	TJ	-65 to +175			°C
Storage Temperature Range	T _{STG}	-65 to +175			°C

Notes:

- 1. 2.0us Pulse Width, f=1.0 KHz
- 2. Pulse Test: 300us Pulse Width, 1% Duty Cycle
- 3. Thermal Resistance from Junction to Case Per Leg, Mount on Heatsink Size of 2 in x 3 in x 0.25in Al-Plate.

Version: A07



RATINGS AND CHARACTERISTIC CURVES (MBR20H100CT - MBR20H200CT)

FIG.1- FORWARD CURRENT DERATING CURVE

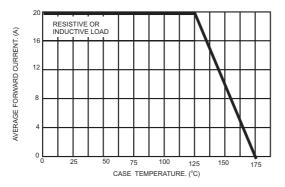


FIG.2- MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT PER LEG

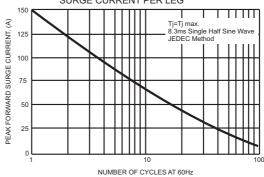


FIG.3- TYPICAL INSTANTANEOUS FORWARD

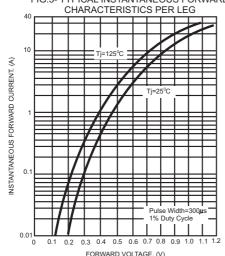


FIG.4- TYPICAL REVERSE CHARACTERISTICS

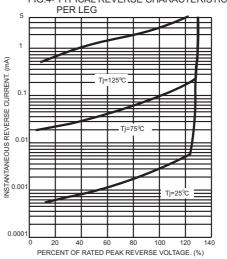


FIG.5- TYPICAL JUNCTION CAPACITANCE PER LEG

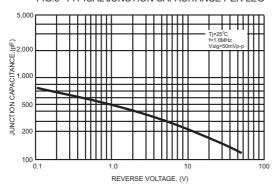


FIG.6- TYPICAL TRANSIENT THERMAL IMPEDANCE

